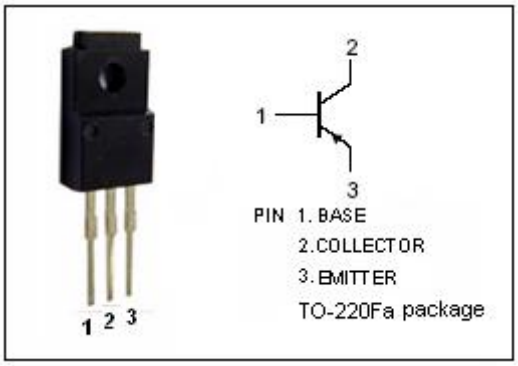
isc Silicon PNP Power Transistor 2SA1651

DESCRIPTION

- Collector-Emitter Breakdown Voltage
  V_{CEO}= -100V(Min)
- Fast switching speed
- Low collector saturation voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

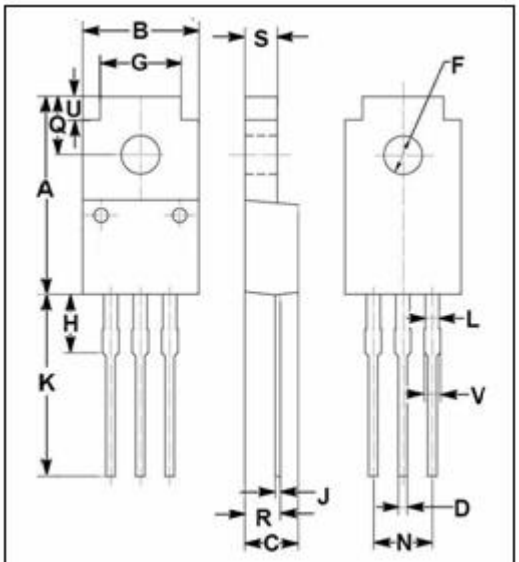


APPLICATIONS

- Designed for TV, monitor vertical output applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-7.0	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-14	A
I_B	Base Current-Continuous	-3.5	A
P_C	Collector Power Dissipation @T_C= 25℃	30	W
	Collector Power Dissipation @T_a= 25℃	1.5	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

isc Silicon PNP Power Transistor 2SA1651

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -0.2A			-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -6A; I_B= -0.3A			-0.5	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= -4A; I_B= -0.2A			-1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= -6A; I_B= -0.3A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE-1}	DC Current Gain	I_C= -0.5A; V_{CE}= -2V	100			
h_{FE-2}	DC Current Gain	I_C= -1.5A; V_{CE}= -2V	100		400	
h_{FE-3}	DC Current Gain	I_C= -4A; V_{CE}= -2V	60			

h_{FE-2} Classifications

M	L	K
100-200	150-300	200-400